

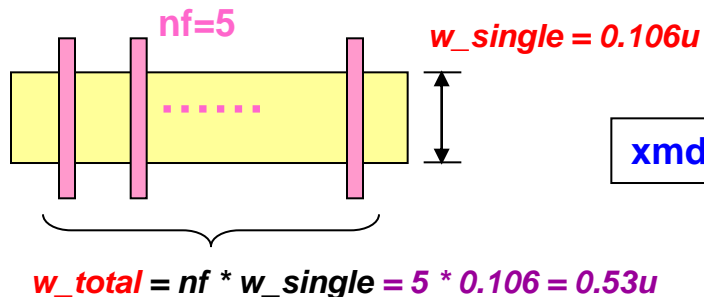
# **FinFET NF parameter & MOS Parallel Reduction**

**July/18, 2014  
PDKD/TSMC**

# NF Handling in Model

## ● BSIM4 Planar Model (N20 and Before)

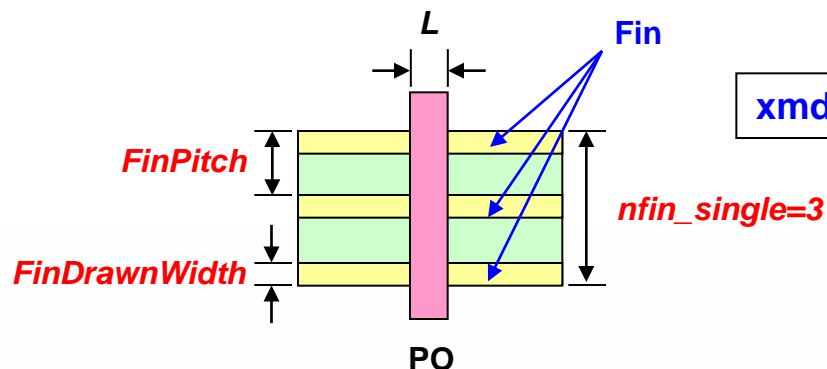
- The input instance  $w = w\_total = nf * w\_single$



```
xmdut d g s b nch_mac w=0.53u l=0.02u nf=5
```

## ● BSIMCMG FinFET Model (N10FF and N16FF)

- The input instance is nfin.
- $nfin = nfin\_single$ .



```
xmdut d g s b nch_mac nfin=3 l=0.02u nf=5
```

# FinFET NF Handling in LVS

- nf can still be used in schematic under following constraints:
  - LVS will translate “nf” into equivalent “m” in schematic side.
  - LVS does not **compare** “nf” parameter.
- The equation of “**nf-to-m**” translation

$$m' = m * \text{nf}$$

- Example of nf-to-m:

**Original schematic:**

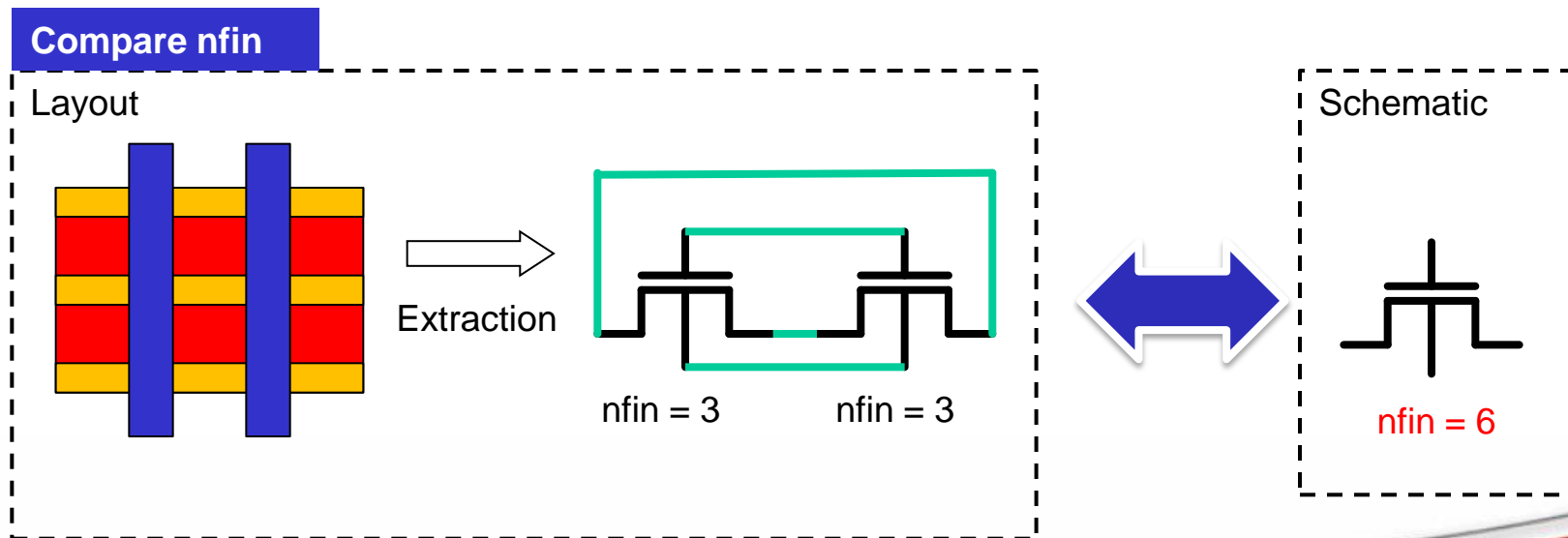
M1 D G S B nch\_svt\_mac nfin=3 l=0.02e-6 **nf=2** m=3

**Translate nf to nfin during LVS execution:**

M1 D G S B nch\_svt\_mac nfin=3 l=0.02e-6 **m=6**

# FinFET MOS Parallel Reduction

- Redefine the behavior of parallel reduction for FinFET process.
- Redefined reduction function in the example below,
  - In layout side:
    - ◆ Two MOS with  $nfin=3$  are extracted.
    - ◆ Sum up  $nfin = 6$
  - In schematic side:
    - ◆ only one MOS with  $nfin=6$ .
  - LVS clean.



# FinFET MOS Parallel Reduction (cont'd)

- Turn on the switch “**LVS\_REDUCE\_PARALLEL\_MOS**” to enable MOS reduction function. Default is off.
- Only MOS with the same length could be reduced.
- **Parallel reduction** equation:

$$\begin{aligned} n_{fin} &= \text{sum}(n_{fin}) \\ l &= \min(l) \end{aligned}$$